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MBR6045WTG

Switch Mode Power Rectifier

The Switch Mode power rectifier employs the use of the Schottky Barrier principle with a Platinum barrier metal.

Features

- Dual Diode Construction; Terminals 1 and 3 May Be Connected for Parallel Operation at Full Rating
- 45 V Blocking Voltage
- Low Forward Voltage Drop
- Guard-ring for Stress Protection and High dv/dt Capability (> 10 V/ns)
- 175°C Operating Junction Temperature
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 4.3 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	45	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Forward Current (Rated V_R , $T_C = 125^\circ\text{C}$)	$I_{F(AV)}$	30 60	A
	Per Diode Per Device		
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, $T_C = 90^\circ\text{C}$)	I_{FRM}	60	A
	Per Diode		
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	500	A
Peak Repetitive Reverse Current (2.0 μs , 1.0 kHz)	I_{RRM}	2.0	A
Storage Temperature Range	T_{stg}	-65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	-65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	°C
Voltage Rate of Change	dv/dt	10,000	V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

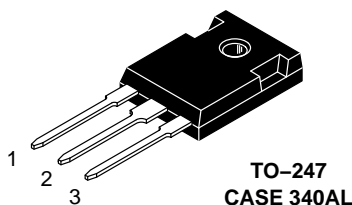
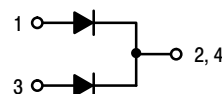
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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SCHOTTKY BARRIER RECTIFIER 60 AMPERES, 45 VOLTS



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MBR6045WTG	TO-247 (Pb-Free)	30 Units/Rail

MBR6045WTG

THERMAL CHARACTERISTICS (Per Diode)

Rating	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS (Per Diode)

Instantaneous Forward Voltage (Note 2) @ $I_F = 30$ Amps, $T_C = 25^{\circ}C$ @ $I_F = 30$ Amps, $T_C = 125^{\circ}C$ @ $I_F = 60$ Amps, $T_C = 25^{\circ}C$	V_F	0.62 0.55 0.75	Volts
Instantaneous Reverse Current (Note 2) @ Rated DC Voltage, $T_C = 25^{\circ}C$ @ Rated DC Voltage, $T_C = 100^{\circ}C$	I_R	1.0 50	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle < 2.0%

TYPICAL ELECTRICAL CHARACTERISTICS

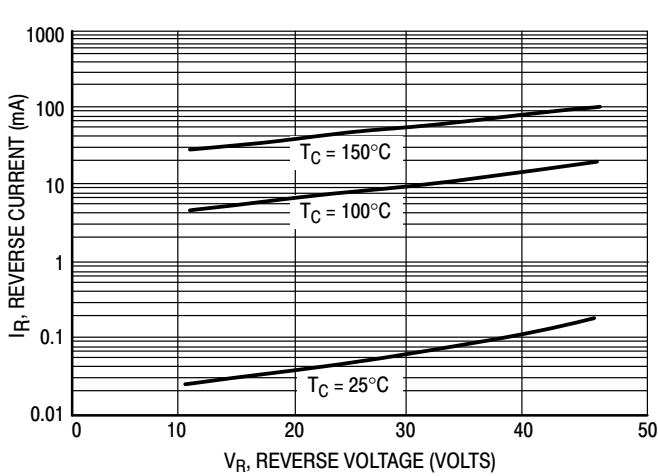


Figure 1. Typical Reverse Current

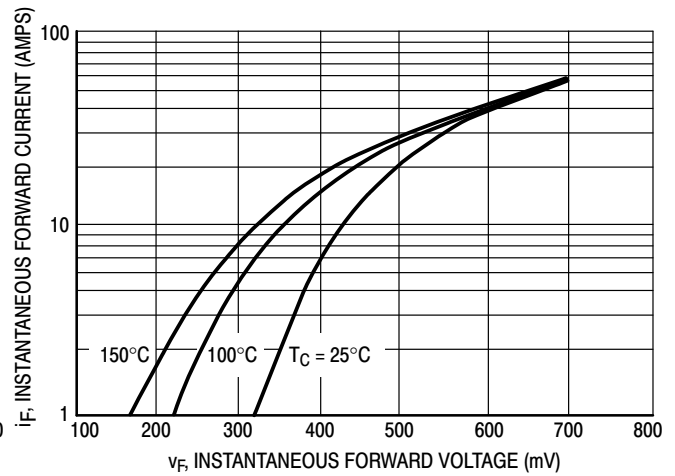
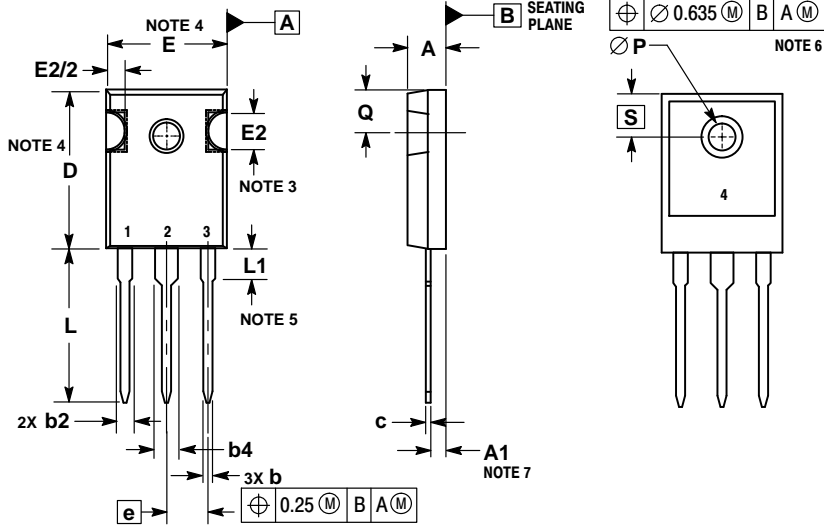


Figure 2. Typical Forward Voltage

MBR6045WTG

PACKAGE DIMENSIONS


TO-247 CASE 340AL ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. $\varnothing P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS	
	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.00	1.40
b2	1.65	2.35
b4	2.60	3.40
c	0.40	0.80
D	20.30	21.40
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
L	19.80	20.80
L1	3.50	4.50
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

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